

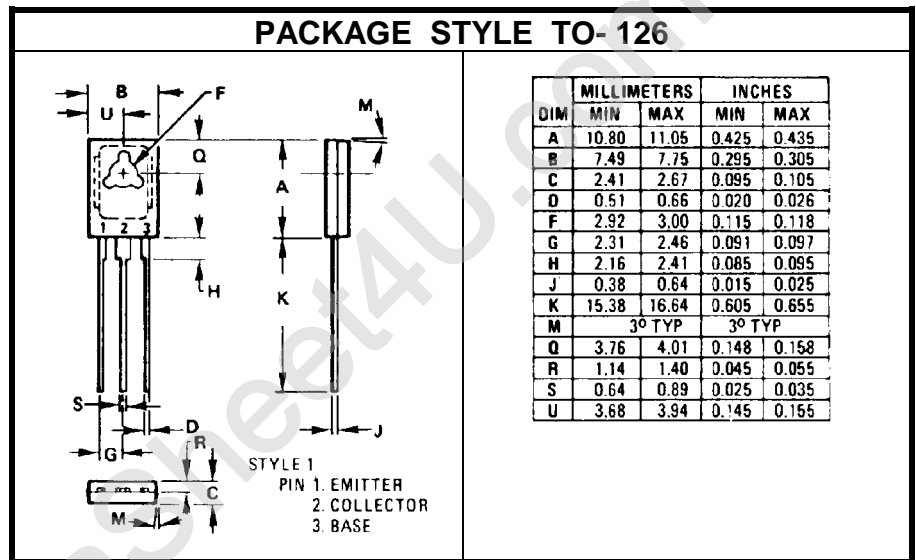
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **ASI BFT51** is Designed for High Frequency Amplifier Applications.

MAXIMUM RATINGS

I_C	500 mA
V_{CE}	20 V
P_{DISS}	3.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+175^\circ\text{C}$
T_{STG}	-65°C to $+175^\circ\text{C}$
θ_{JC}	20 K/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$	10			V
BV_{CER}	$I_C = 10\text{ mA}$ $R_{BE} = 100\ \Omega$	19			V
BV_{CBO}	$I_C = 5.0\text{ mA}$	20			V
BV_{EBO}	$I_C = 1.0\text{ mA}$	3.0			V
I_{CES}	$V_{CE} = 10\text{ V}$			100	μA
H_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	40			---
	$I_C = 300\text{ mA}$	50			
f_t	$V_{CE} = 5.0\text{ V}$ $I_C = 300\text{ mA}$ $f = 100\text{ MHz}$	1.0	2.0		GHz
C_{cb}	$V_{CB} = 5.0\text{ V}$ $f = 1.0\text{ MHz}$		4.2		Pf
C_C	$V_{CB} = 5.0\text{ V}$ $f = 1.0\text{ MHz}$		5.8		Pf